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## Supplemental material for publication

## Magnetic and electronic properties of 2D $TiX_3$ (X = F, Cl, Br, I)

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Table S1. Calculated lattice constants (Å) of TiX<sub>3</sub> monolayers with different U-J values

U-J/eV	3	4	5	6
TiF <sub>3</sub>	5.55	5.61	5.62	5.63
TiCl <sub>3</sub>	6.29	6.33	6.35	6.38
$TiBr_3$	6.65	6.66	6.68	6.68
$TiI_3$	7.15	7.19	7.20	7.21

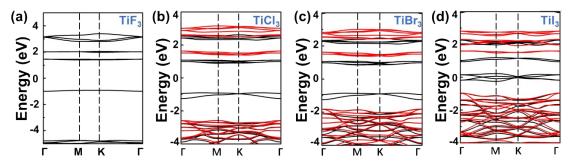


Fig. S1 Electronic band structures of (a) TiF<sub>3</sub>, (b) TiCl<sub>3</sub>, (c) TiBr<sub>3</sub> and (d) TiI<sub>3</sub> calculated with U-J = 3 eV from the DFT + U method. The Fermi level was set to 0 eV.  $\Gamma$  (0, 0, 0), M (1/2, 0, 0), and K (1/3, 1/3, 0) are highly symmetric points in reciprocal space. Red - spin down; black - spin up.

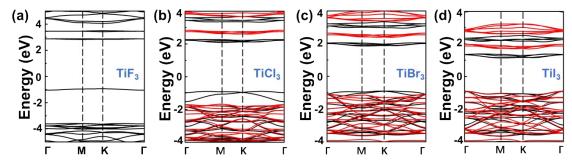


Fig. S2 Electronic band structures of (a)  $TiF_3$ , (b)  $TiCl_3$ , (c)  $TiBr_3$  and (d)  $TiI_3$  calculated with U-J = 5 eV from the DFT + U method. The Fermi level was set to 0 eV.  $\Gamma$  (0, 0, 0), M (1/2, 0, 0), and K (1/3, 1/3, 0) are highly symmetric points in reciprocal space. Red - spin down; black - spin up.

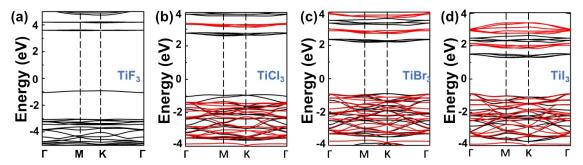


Fig. S3 Electronic band structures of (a)  $TiF_3$ , (b)  $TiCl_3$ , (c)  $TiBr_3$  and (d)  $TiI_3$  calculated with U-J = 6 eV from the DFT + U method. The Fermi level was set to 0 eV.  $\Gamma$  (0, 0, 0), M (1/2, 0, 0), and K (1/3, 1/3, 0) are highly symmetric points in reciprocal space. Red - spin down; black - spin up.

Table S2 Band gaps (eV) of TiX3 monolayers with different U-J values

U-J/eV	3	4	5	6
TiF <sub>3</sub>	2.32	3.04	3.77	4.49
TiCl <sub>3</sub>	1.79	2.39	2.99	3.52
TiBr <sub>3</sub>	1.70	2.27	2.76	3.09
TiI <sub>3</sub>	0.02	1.91	2.05	2.18

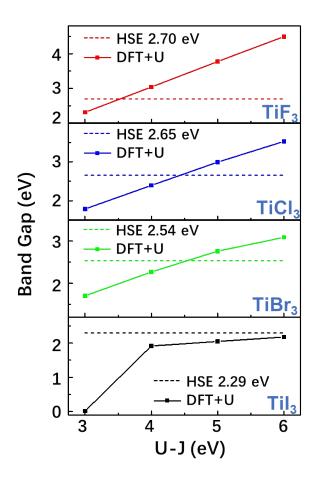


Fig. S4 Band gap of (a)  $TiF_3$ , (b)  $TiCl_3$ , (c)  $TiBr_3$  and (d)  $TiI_3$  as a function of U compared with the band gaps calculated with HSE06.

Tab. S3 Calculated total magnetic moments per unit cell ( $M_{tot}$ ), local Magnetic moments of Ti ( $M_{Ti}$ ) and Br/I ( $M_X$ ) in monolayer TiBr<sub>3</sub> and TiI<sub>3</sub>

	TiBr <sub>3</sub>			TiI <sub>3</sub>		
	FM	AFM-N	AFM-z	FM	AFM-N	AFM-z
$M_{tot}(\mu b)$	1.71	0	0	1.72	0	-0.02
$M_{\text{Ti}}(\mu b)$	0.98	-0.95/0.95	-0.97/0.97	1.04	-1.01/1.01	-1.02/1.02
$M_X(\mu b)$	-0.04	0	-0.04/0.04	-0.06	0	-0.05/0.05

Tab. S4 Exchange energies  $(E_{ex})$  of  $TiX_3$  monolayers (per  $TiX_3$  formula meV/s.f.) with different U-J values

U-J/eV	3	4	5	6
TiF <sub>3</sub>	-2.01	-3.01	-1.67	-1.28
TiCl <sub>3</sub>	4.23	3.94	2.10	1.72
TiBr <sub>3</sub>	3.88	27.54	27.39	27.56
$TiI_3$	3.56	26.24	25.68	26.01